Features

- Operated at Low Logic Level Gate Drive
- P-Channel Switch with Low $R_{DS(on)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-Channel MOSFET

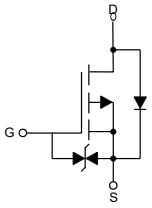
Maximum Ratings

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Maximum Thermal Resistance: 1250°C/W Junction to Ambient

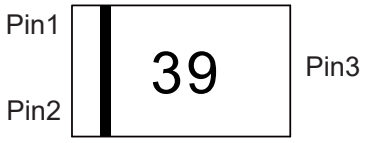
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous[2]	I_D	-0.66	A
Pulsed Drain Current	I_{DM}	-1.2	A
Power Dissipation[3]	P_D	0.10	W

Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

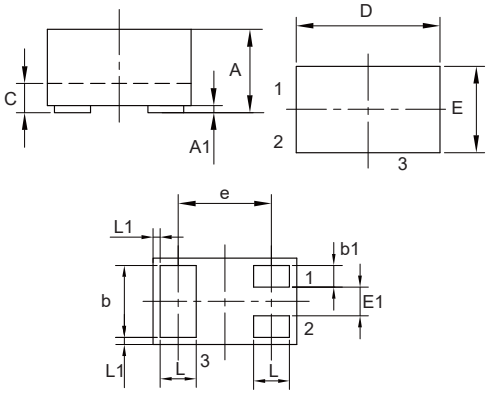
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

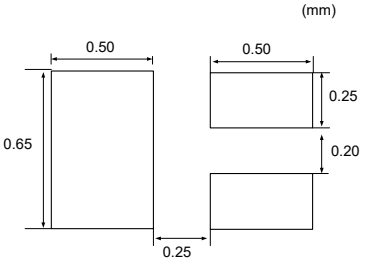


DFN1006-3



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.018	0.022	0.45	0.55	
A1	0.000	0.002	0.00	0.05	
b	0.018	0.022	0.45	0.55	
b1	0.004	0.008	0.10	0.20	
c	0.005	0.007	0.12	0.18	
D	0.037	0.042	0.95	1.075	
E	0.022	0.026	0.55	0.675	
E1	0.006	0.010	0.15	0.25	
e	0.026		0.65		TYP.
L	0.008	0.012	0.20	0.30	
L1	0.0002		0.05		TYP.

Suggested Solder Pad Layout



ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-20			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.35	-0.61	-1.1	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-20V, V_{GS} =0V			-1.0	μA
Gate-body Leakage Current	I_{GSS}	V_{GS} =±10V, V_{DS} =0V			±20	μA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V, I_D=-1000mA		0.45	0.52	Ω
		V_{GS}=-2.5V, I_D=-800mA		0.65	0.78	
		V_{GS}=-1.8V, I_D=-500mA		0.95		
Forward transconductance	g_{FS}	V_{DS}=-10V, I_D=-540mA		1.2		S
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-500mA			-1.2	V
Dynamic Characteristics						
Input Capacitance(4)	C_{iss}	V_{DS}=-16V,V_{GS}=0V, f=1MHz		113		pF
Output Capacitance(4)	C_{oss}			15		
Reverse Transfer Capacitance(4)	C_{rss}			9		
Switching Characteristics						
Turn-on Delay Time(5)	$t_{d(on)}$	V_{DS}=-10V,V_{GS}=-4.5V,I_D=-200mA, R_{GEN}=10Ω		9.0		ns
Turn-off Delay Time(5)	$t_{d(off)}$			32.6		
Rise Time(5)	t_r			5.7		
Fall Time(5)	t_f			20.3		

Note:

2. Surface Mounted on FR4 board using the minimum recommended pad size.
3. Pulse Test: Pulse width ≤300μs,duty cycle≤2%.
4. Graranteed by design, not subject to productin
5. Switching characteristics are independent of operating junction temperatures.

Curve Characteristics

Fig. 1 - Output Characteristics

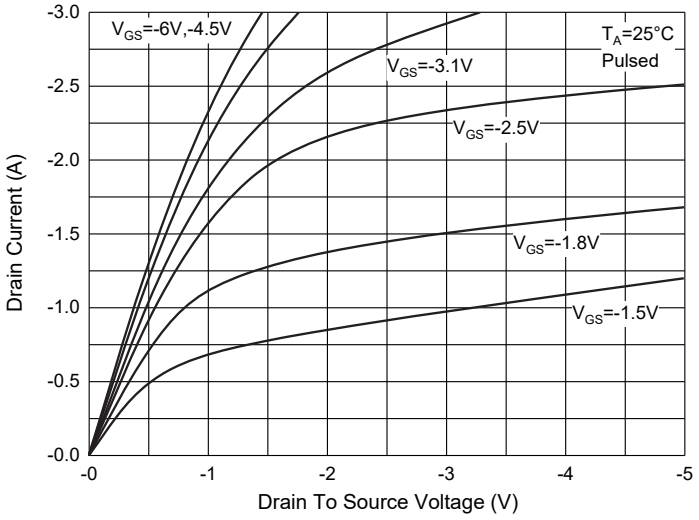


Fig. 2 - Transfer Characteristics

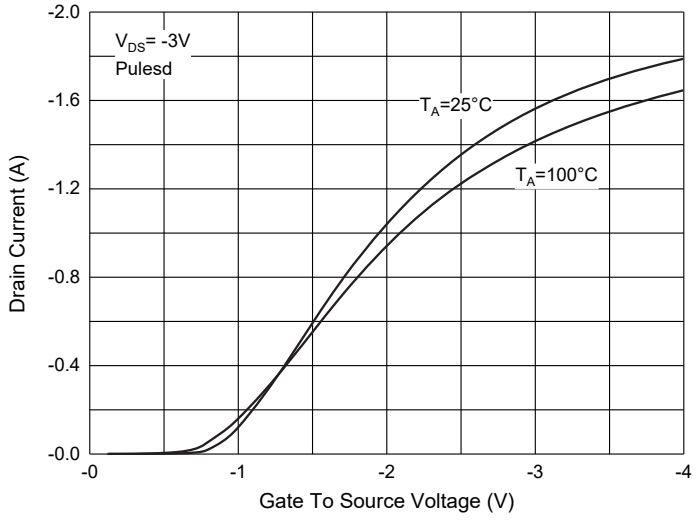


Fig. 3 - $R_{DS(ON)}$—I_D

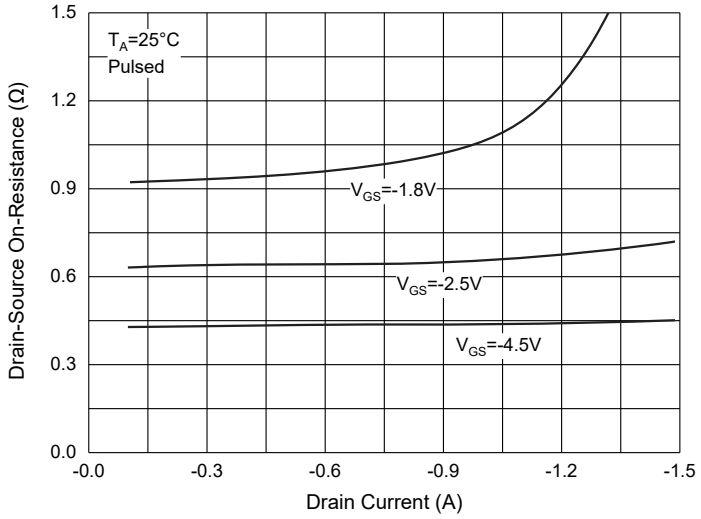


Fig. 4 - $R_{DS(ON)}$—V_{GS}

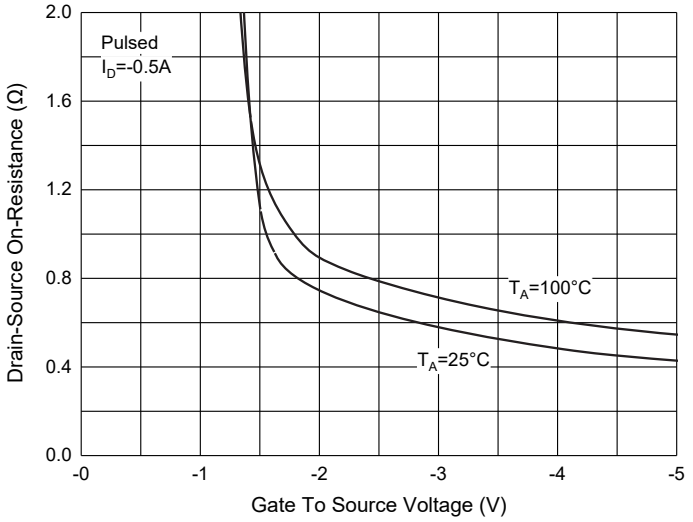


Fig. 5 - I_S—V_{SD}

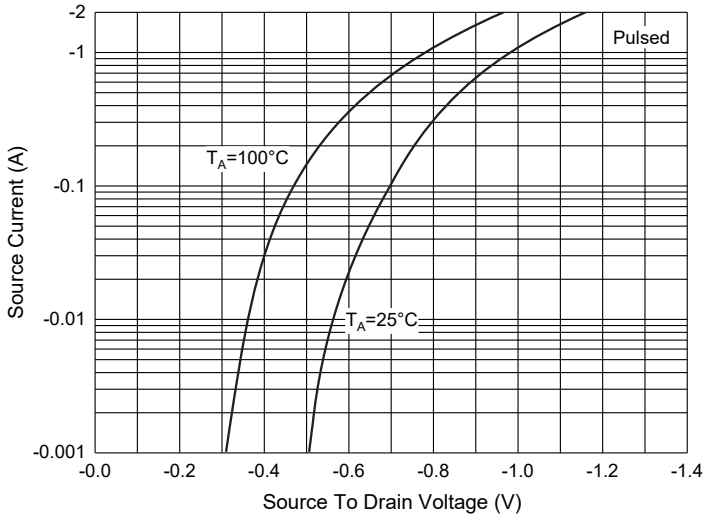
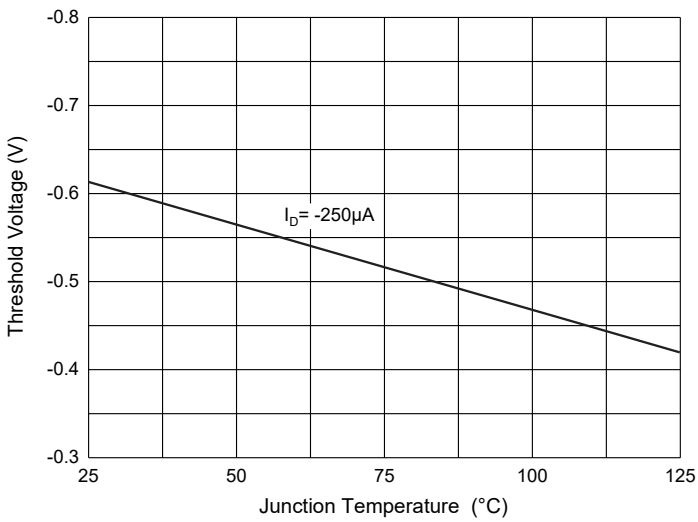


Fig. 6 - Threshold Voltage



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:10Kpcs/Reel